

2SB554

SILICON PNP TRIPLE DIFFUSED TYPE

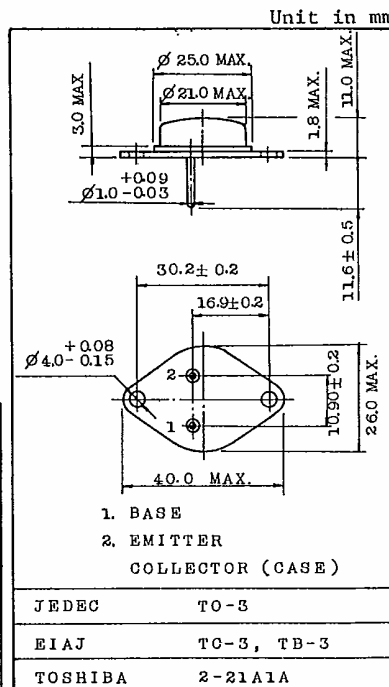
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- High Power Dissipation : $P_C = 150W$
- High Breakdown Voltage : $V_{CE0} = -180V$
- Complementary to 2SD424.
- Recommended for 100W High-Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-180	V
Collector-Emitter Voltage	V_{CE0}	-180	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-15	A
Emitter Current	I_E	15	A
Collector Power Dissipation ($T_c = 25^\circ C$)	P_C	150	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-65 ~ 150	$^\circ C$



Mounting Kit No. AC73
Weight : 12.9g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{C0}	$V_{CB}=-90V, I_E=0$	-	-	-100	μA
Emitter Cut-off Current	I_{E0}	$V_{EB}=-5V, I_C=0$	-	-	-100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CE0}$	$I_C=-0.1A, I_B=0$	-180	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EB0}$	$I_E=-10mA, I_C=0$	-5	-	-	V
DC Current Gain	h_{FE} (Note)	$V_{CE}=-5V, I_C=-2A$	40	-	140	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-10A, I_B=-1A$	-	-	-3.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-5V, I_C=-10A$	-	-	-2.5	V
Transition Frequency	f_T	$V_{CE}=-5V, I_C=-2A$	-	6	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	450	-	pF

Note: h_{FE} Classification R : 40 ~ 80, O : 70 ~ 140

TOSHIBA CORPORATION

